NSN 5961-01-457-7359

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-457-7359 **Inclosure Material:** Ceramic **Overall Length:** Between 0.690 inches and 0.785 inches **Overall Height:** Between 0.080 inches and 0.140 inches Overall Width: Between 0.290 inches and 0.325 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 drain to source voltage all transistor and 20.0 gate to source voltage all transistor **Power Rating Per Characteristic:** 2.0 watts total device dissipation all transistor **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Test Data Document:** 78711-t5961-0002 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli